

# IRFL4315PbF

HEXFET® Power MOSFET

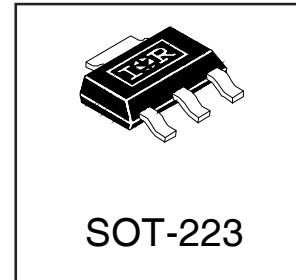
## Applications

- High frequency DC-DC converters

$V_{DSS}$	$R_{DS(on) \max}$	$I_D$
150V	185mΩ@ $V_{GS} = 10V$	2.6A

## Benefits

- Low Gate to Drain Charge to Reduce Switching Losses
- Fully Characterized Capacitance Including Effective  $C_{OSS}$  to Simplify Design, (See App. Note AN1001)
- Fully Characterized Avalanche Voltage and Current
- Lead-Free



## Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	2.6	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	2.1	
$I_{DM}$	Pulsed Drain Current ①	21	
$P_D @ T_A = 25^\circ C$	Power Dissipation②	2.8	W
	Linear Derating Factor	0.02	W/°C
$V_{GS}$	Gate-to-Source Voltage	± 30	V
dv/dt	Peak Diode Recovery dv/dt ③	6.3	V/ns
$T_J$	Operating Junction and	-55 to + 150	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case )	

## Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount, steady state)④	—	45	°C/W

Notes ① through ⑥ are on page 8  
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International  
**IR** Rectifier

## Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	150	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.19	—	V/°C	Reference to $25^\circ\text{C}$ , $I_D = 1\text{mA}$ ③
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	185	mΩ	$V_{GS} = 10V, I_D = 1.6A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	3.0	—	5.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	25	μA	$V_{DS} = 150V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 120V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 30V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -30V$

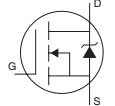
## Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$g_{fs}$	Forward Transconductance	3.5	—	—	S	$V_{DS} = 50V, I_D = 1.6A$
$Q_g$	Total Gate Charge	—	12	19	nC	$I_D = 1.6A$
$Q_{gs}$	Gate-to-Source Charge	—	2.1	3.1		$V_{DS} = 120V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	6.8	10		$V_{GS} = 10V$
$t_{d(on)}$	Turn-On Delay Time	—	8.4	—	ns	$V_{DD} = 75V$
$t_r$	Rise Time	—	21	—		$I_D = 1.6A$
$t_{d(off)}$	Turn-Off Delay Time	—	20	—		$R_G = 15\Omega$
$t_f$	Fall Time	—	19	—		$V_{GS} = 10V$ ③
$C_{iss}$	Input Capacitance	—	420	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	100	—		$V_{DS} = 25V$
$C_{rss}$	Reverse Transfer Capacitance	—	25	—		$f = 1.0\text{MHz}$
$C_{oss}$	Output Capacitance	—	720	—		$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0\text{MHz}$
$C_{oss}$	Output Capacitance	—	48	—		$V_{GS} = 0V, V_{DS} = 120V, f = 1.0\text{MHz}$
$C_{oss\ eff.}$	Effective Output Capacitance	—	98	—		$V_{GS} = 0V, V_{DS} = 0V\ \text{to}\ 120V$ ③

## Avalanche Characteristics

	Parameter	Typ.	Max.	Units
$E_{AS}$	Single Pulse Avalanche Energy②	—	38	mJ
$I_{AR}$	Avalanche Current①	—	3.1	A

## Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	2.6	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	21		
$V_{SD}$	Diode Forward Voltage	—	—	1.5	V	$T_J = 25^\circ\text{C}, I_S = 2.1A, V_{GS} = 0V$ ③
$t_{rr}$	Reverse Recovery Time	—	61	91	ns	$T_J = 25^\circ\text{C}, I_F = 1.6A$
$Q_{rr}$	Reverse Recovery Charge	—	160	240	nC	$di/dt = 100A/\mu s$ ③

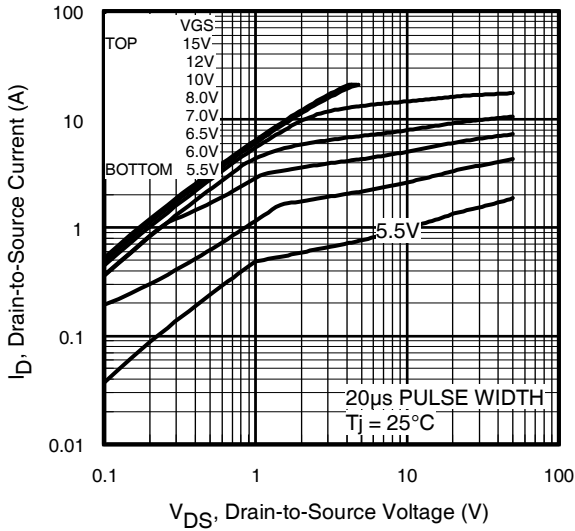


Fig 1. Typical Output Characteristics

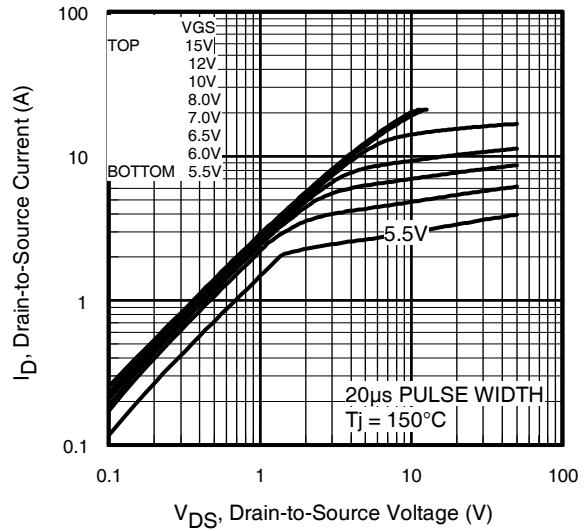


Fig 2. Typical Output Characteristics

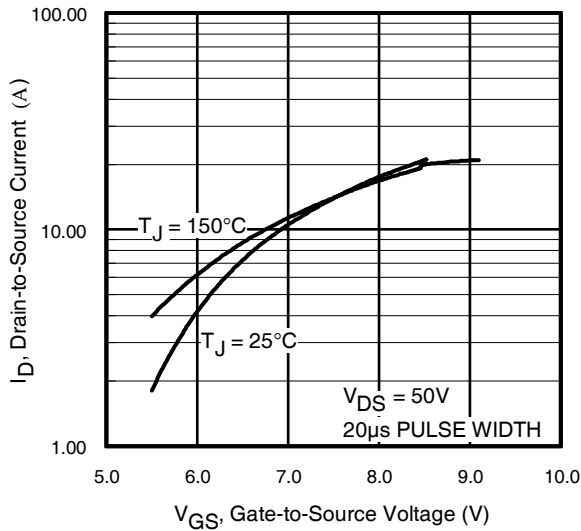


Fig 3. Typical Transfer Characteristics

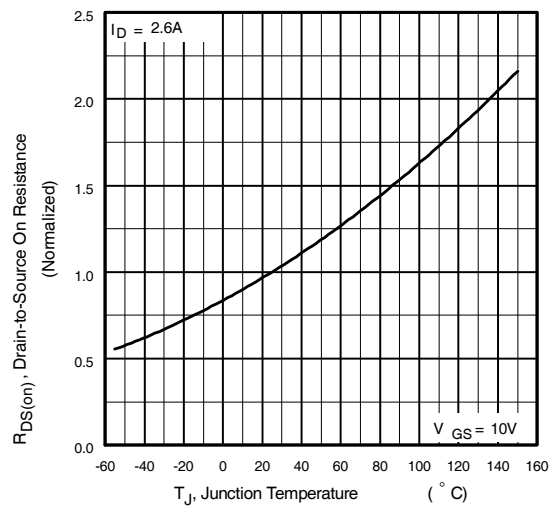
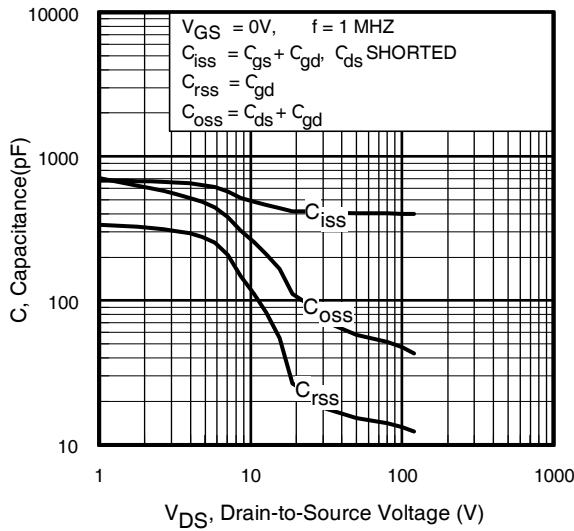


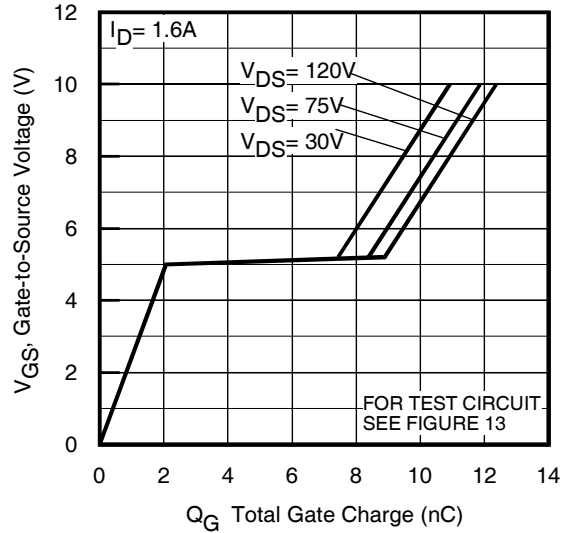
Fig 4. Normalized On-Resistance Vs. Temperature

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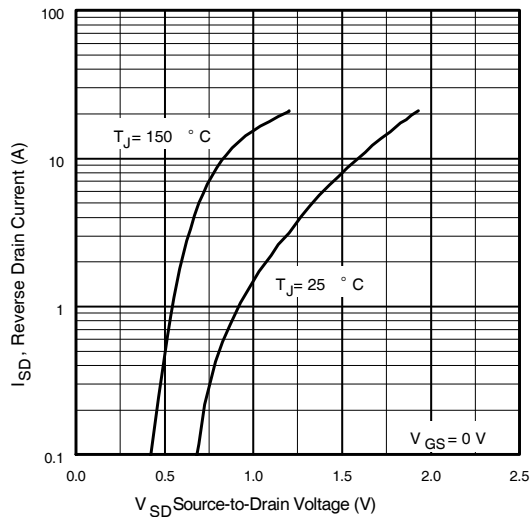
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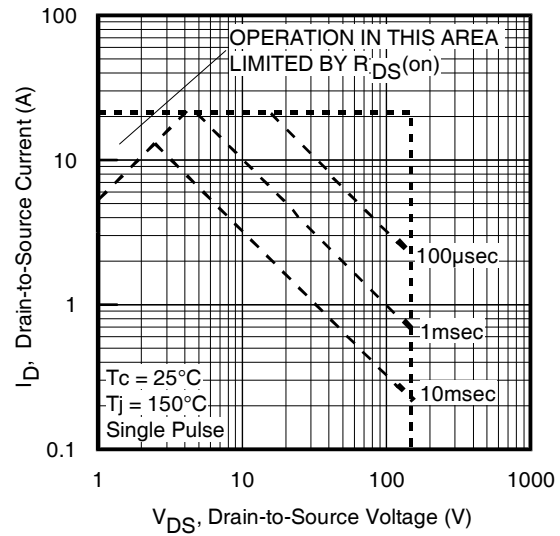
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



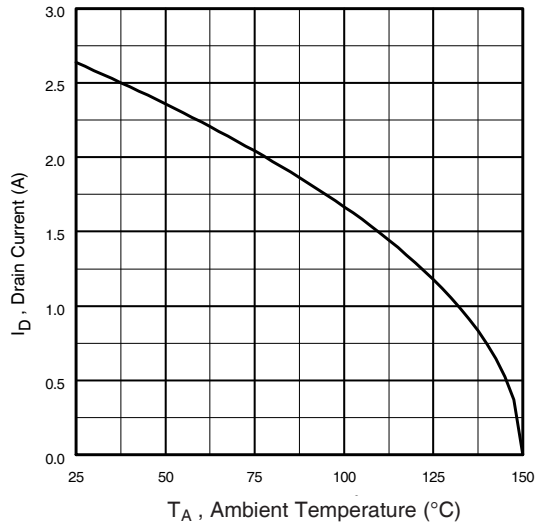
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



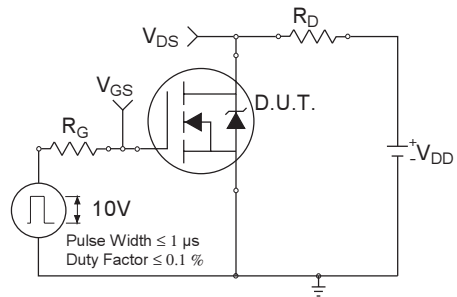
**Fig 7.** Typical Source-Drain Diode Forward Voltage



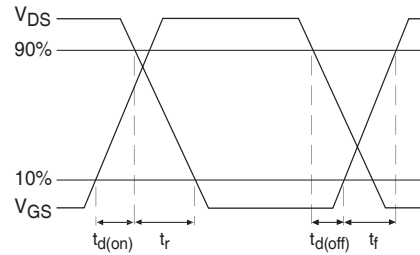
**Fig 8.** Maximum Safe Operating Area



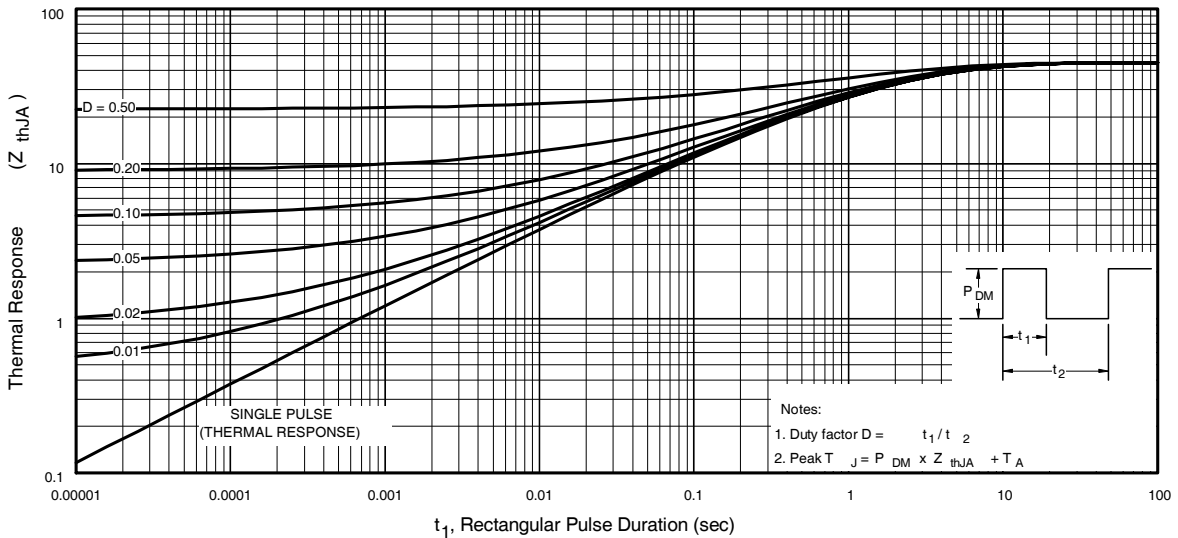
**Fig 9.** Maximum Drain Current Vs. Ambient Temperature



**Fig 10a.** Switching Time Test Circuit



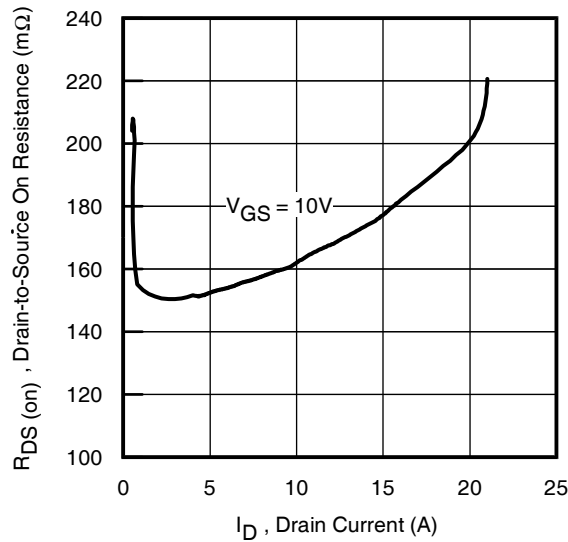
**Fig 10b.** Switching Time Waveforms



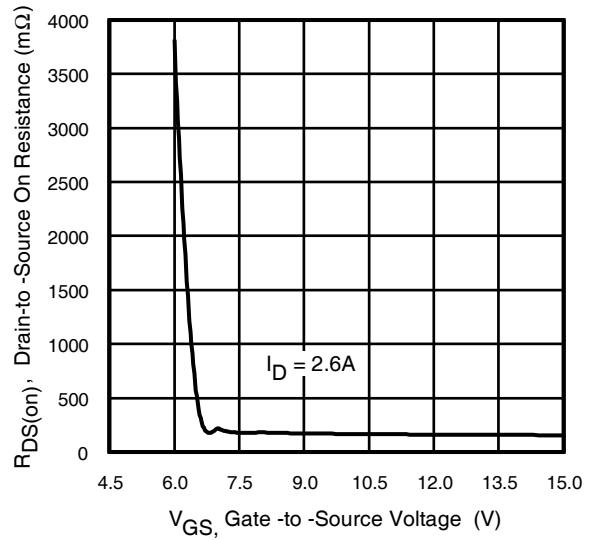
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

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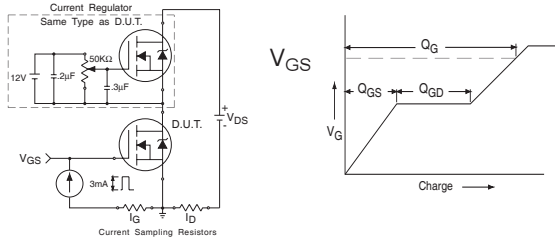
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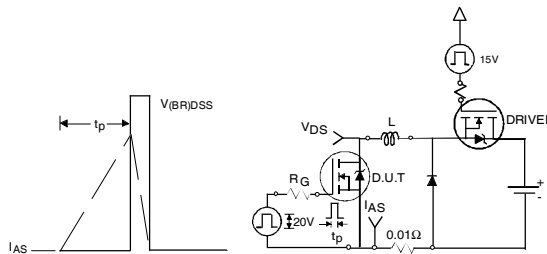
**Fig 12.** On-Resistance Vs. Drain Current



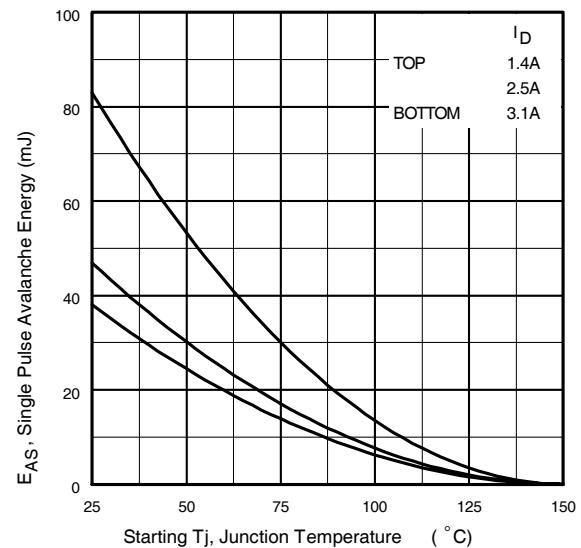
**Fig 13.** On-Resistance Vs. Gate Voltage



**Fig 14a&b.** Basic Gate Charge Test Circuit and Waveform



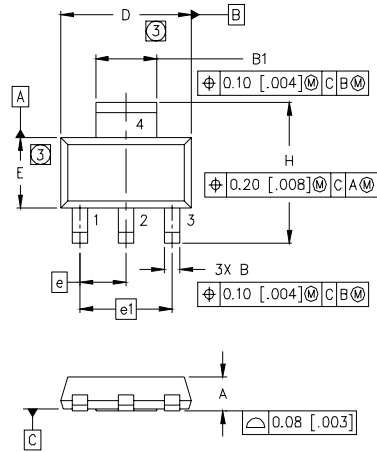
**Fig 15a&b.** Unclamped Inductive Test circuit and Waveforms



**Fig 15c.** Maximum Avalanche Energy Vs. Drain Current

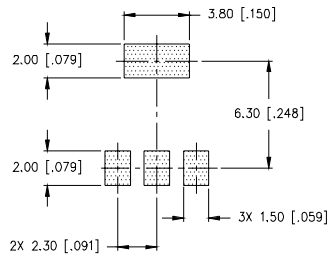
## SOT-223 (TO-261AA) Package Outline

Dimensions are shown in millimeters (inches)



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.55	1.80	.061	.071
B	0.65	0.85	.026	.033
B1	2.95	3.15	.116	.124
C	0.25	0.35	.010	.014
D	6.30	6.70	.248	.264
E	3.30	3.70	.130	.146
e	2.30	BSC	.0905	BSC
e1	4.60	BSC	.181	BSC
H	6.71	7.29	.264	.287
L	0.91	—	.036	—
L1	0.061	BSC	.0024	BSC
θ	—	10°	—	10°

### MINIMUM RECOMMENDED FOOTPRINT



### LEAD ASSIGNMENTS

- 1 = GATE
- 2 = DRAIN
- 3 = SOURCE
- 4 = DRAIN

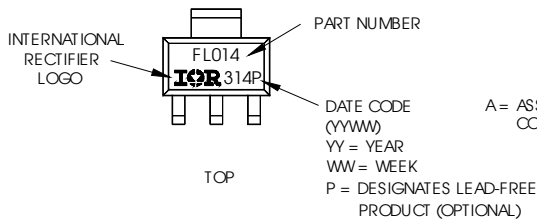
### NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS DO NOT INCLUDE MOLD FLASH.
4. OUTLINE CONFORMS TO JEDEC OUTLINE TO-261AA.
5. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].

## SOT-223 (TO-261AA) Part Marking Information

### HEXFET PRODUCT MARKING

EXAMPLE: THIS IS AN IRFL014



### Notes:

1. For an Automotive Qualified version of this part please see <http://www.irf.com/product-info/auto/>
2. For the most current drawing please refer to IR website at <http://www.irf.com/package/>

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